

# CHIP MONOLITHIC CERAMIC CAPACITOR FOR AUTOMOTIVE GCM1885C1H201JA16 $\_$ (0603, C0G, 200pF, 50Vdc)

\_: packaging code

**Reference Sheet** 

# 1.Scope

This product specification is applied to Chip Monolithic Ceramic Capacitor used for Automotive Electronic equipment.

#### 2.MURATA Part NO. System

(Ex.)	GCM	18	8	5C	1H	201	J	A16	D
		(1)L/W Dimensions	(2)T Dimensions	(3)Temperature Characteristics	(4)DC Rated Voltage	(5)Nominal Capacitance	(6)Capacitance Tolerance	(7)Murata's Control Code	(8)Packaging Code

#### 3. Type & Dimensions



(Unit:mm)

1

(1)-1 L	(1)-2 W	(2) T	е	g
1.6±0.1	0.8±0.1	0.8±0.1	0.2 to 0.5	0.5 min.

#### 4.Rated value

` ,	(3) Temperature Characteristics (Public STD Code):C0G(EIA)			(6) Capacitance	Specifications and Test Methods	
Temp. coeff or Cap. Change	Temp. Range (Ref.Temp.)	DC Rated Voltage	Capacitance	Tolerance	(Operationg Temp. Range)	
0±30 ppm/°C	25 to 125 °C (25 °C)	50 Vdc	200 pF	±5 %	-55 to 125 °C	

5.Package

mark	(8) Packaging	Packaging Unit
D	φ180mm Reel PAPER W8P4	4000 pcs./Reel
J	φ330mm Reel PAPER W8P4	10000 pcs./Reel

Product specifications in this catalog are as of Jan.25,2013,and are subject to change or obsolescence without notice. Please consult the approval sheet before ordering.

Please read rating and !Cautions first.

	Specification.							
No	AEC-Q200	Test Item	Temperature Compensating Type	High Dielectric Type		A	AEC-Q200 Test Metho	od
1	Pre-and Post-S Electrical Test				-			
2	High Temperat	ture	The measured and observed charac	teristics should satisfy the	Set the capa	citor for 1000±	±12 hours at 150±3℃.	Set for
	Exposure (Stor	rage)	specifications in the following table.		24±2 hours at room temperature, then measure.			
		Appearance	No marking defects		1			
		Capacitance	Within ±2.5% or ±0.25pF	R7/L8/R9: Within ±10.0%	1			
		Change	(Whichever is larger)					
		Q/D.F.	30pFmin. : Q≧1000	R7/L8 W.V.: 25Vmin.: 0.03 max.	Ī			
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.05 max.				
			C: Nominal Capacitance(pF)	R9 : 0.075max.				
		I.R.	More than 10,000MΩ or 500Ω •F					
			(Whichever is smaller)					
2	Temperature C	Cycling	R9 : More than 150Ω •F		F: 0	2		
3	remperature C	yciing	The measured and observed charac	teristics should satisfy the			pporting jig in the same	
			specifications in the following table.		+	,	9). Perform cycle test a	•
		Appearance	No marking defects	T	+		e following table. Set f	or 24±2 hours at
		Capacitance	·		room temper	rature, then me	easure	
		Change	(Whichever is larger)		↓ ┌─		٥	aloc I
		Q/D.F.	30pFmin. : Q≧1000	R7/L8 W.V.: 25Vmin.: 0.03 max.	Step	Time (min)	<u> </u>	200 (for 56 /1 9 /P0)
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.05 max.		15±3	1000 (for △ C/R7) -55°C+0/-3	300 (for 5G/L8/R9) -55°C+0/-3
			C: Nominal Capacitance(pF)	R9: 0.05max.	2	10 = 3	-55 C+0/-3 Room	-55 C+U/-3 Room
					3	15±3	125°C+3/-0	150°C+3/-0
		I.R.	More than $10,000M\Omega$ or $500\Omega$ •F		4	10.10	Room	Room
			(Whichever is smaller)		4		ROUII	NUUIII
					· Initial meas	surement for h	igh dielectric constant	type
					Perform a he	eat treatment a	at 150+0/-10 °C for one	e hour and then set
					for 24±2 hou	irs at room ten	nperature.	
					Perform the	initial measure	ement.	
	Destructive		No defects or abnormalities		Per EIA-469			
_	Phisical Analys							
5	Moisture Resis	stance	The measured and observed character	teristics should satisfy the	Annhitha 24	hour hoot (25	to 65°C) and humidity	
						,	,	(80 to 98%)
- 1			specifications in the following table.		treatment sh	own below, 10	consecutive times.	
		Appearance	specifications in the following table.  No marking defects		treatment sh	own below, 10	,	
		Appearance Capacitance	, ,	R7/L8/R9: Within ±12.5%	treatment sh	own below, 10 2 hours at roor	consecutive times.  m temperature, then m	neasure. Humidity
			No marking defects	,	treatment sh Set for 24±2 Temperature (°C)	own below, 10	consecutive times.  m temperature, then m	neasure.
		Capacitance	No marking defects Within ±3.0% or ±0.30pF	,	treatment sh Set for 24±2	own below, 10 2 hours at roor	consecutive times.  m temperature, then m  Humidity  80~98% Humidity	neasure. Humidity 80~98% Humidity
		Capacitance Change	No marking defects Within ±3.0% or ±0.30pF (Whichever is larger)	R7/L8/R9: Within ±12.5%	treatment sh Set for 24±: Temperature (°C) 70 65 60	own below, 10 2 hours at roor	consecutive times.  m temperature, then m  Humidity  80~98% Humidity	neasure. Humidity 80~98% Humidity
		Capacitance Change	No marking defects  Within ±3.0% or ±0.30pF  (Whichever is larger)  30pFmin. : Q≧350	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 55 50	own below, 10 2 hours at roor	consecutive times.  m temperature, then m  Humidity  80~98% Humidity	neasure. Humidity 80~98% Humidity
		Capacitance Change	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin. : Q≧350  10pF and over, 30pF and below:	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.	Treatment sh Set for 24±:  Temperature (°C) 70 65 60 55 50 45	own below, 10 2 hours at roor	consecutive times.  m temperature, then m  Humidity  80~98% Humidity	neasure. Humidity 80~98% Humidity
		Capacitance Change	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin. : Q≧350  10pF and over, 30pF and below: Q≥275+5C/2	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 55 50 40 40 35 30	own below, 10 2 hours at roor	consecutive times.  m temperature, then m  Humidity  80~98% Humidity	neasure. Humidity 80~98% Humidity
		Capacitance Change	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin. : Q≧350  10pF and over, 30pF and below: Q≥275+5C/2  10pFmax.: Q ≥200+10C	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 55 40 45 40 35 30 25	own below, 10 2 hours at roor Humidity 90~98%	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98%	neasure. Humidity 80~98% Humidity
		Capacitance Change Q/D.F.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin. : Q≧350  10pF and over, 30pF and below: Q≧275+5C/2  10pFmax.: Q ≥200+10C C: Nominal Capacitance(pF)	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.	Treatment sh Set for 24±:  Temperature (°C) 70 65 60 55 50 45 40 35 30 25 20 15	own below, 10 2 hours at roor Humidity 90~98%	consecutive times.  m temperature, then m  Humidity  80~98% Humidity	neasure. Humidity 80~98% Humidity
		Capacitance Change Q/D.F.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≧350  10pF and over, 30pF and below: Q≧275+5C/2  10pFmax.: Q ≥200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω · F	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 95 50 45 40 35 30 25 20	own below, 10 2 hours at roor Humidity 90~98%	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98%	neasure. Humidity 80~98% Humidity
		Capacitance Change Q/D.F.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≧350  10pF and over, 30pF and below: Q≧275+5C/2  10pFmax.: Q ≧200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω •F (Whichever is smaller)	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.	Treatment sh Set for 24±:  Temperature (°C) 70 65 60 55 50 45 40 35 30 25 20 15 10 5 Init	own below, 10 2 hours at roor Humidity 90~98%	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98%	neasure. Humidity 80~98% Humidity
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		Capacitance Change Q/D.F.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≧350  10pF and over, 30pF and below: Q≧275+5C/2  10pFmax.: Q ≧200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω •F (Whichever is smaller)	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 55 50 45 40 35 30 25 20 15 10 5 111 5 111 115 0 -5 -10	own below, 10 2 hours at roor  Humidity 90~98%	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 10.2°C	Humidity 80~98% Humidity 90~98%
		Capacitance Change Q/D.F.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≧350  10pF and over, 30pF and below: Q≧275+5C/2  10pFmax.: Q ≧200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω •F (Whichever is smaller)	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 55 50 45 40 35 30 25 20 15 10 5 111 5 111 115 0 -5 -10	own below, 10 2 hours at roor  Humidity 90~98%	Consecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98%	Humidity 80~98% Humidity 90~98%
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6	Biased Humidi	Capacitance Change Q/D.F.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≧350  10pF and over, 30pF and below: Q≧275+5C/2  10pFmax.: Q ≧200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω •F (Whichever is smaller)	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.  R9: 0.075max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 40 45 40 35 30 25 20 15 10 5 11it	own below, 10 2 hours at roor  Humidity 90~98%	Oconsecutive times.  In temperature, then in Humidity 90~98% Humidity 90~98% Humidity 10.2°C One cycle 24hours 8 9 10 11 12 13 14 15 11	heasure.  Humidity 80~98% Humidity 90~98% 6 17 18 19 20 21 22 23 24
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6	Biased Humidi	Capacitance Change Q/D.F.	No marking defects  Within $\pm 3.0\%$ or $\pm 0.30$ pF (Whichever is larger) $30$ pFmin. : $Q \ge 350$ $10$ pF and over, $30$ pF and below: $Q \ge 275 + 5$ C/2 $10$ pFmax.: $Q \ge 200 + 10$ C C: Nominal Capacitance(pF)  More than $10,000$ M $\Omega$ or $500\Omega$ ·F (Whichever is smaller)  R9: More than $150\Omega$ ·F	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.  R9: 0.075max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 40 45 40 35 30 25 10 15 10 -5 -10 Apply the rat at 85±3°C ar	own below, 10 2 hours at roor  Humidity 90~98%  1 1 2 3 4 5 6 :	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 90~98%  One cycle 24hours  Hours  d 1.3+0.2/-0vdc (add 6	neasure.  Humidity 80~98% Humidity 90~98%  6 17 18 19 20 21 22 23 24  5.8kΩ resister)  nours.
6	Biased Humidi	Capacitance Change Q/D.F.  I.R.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≥350  10pF and over, 30pF and below: Q≥275+5C/2  10pFmax.: Q≥200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω · F (Whichever is smaller)  R9: More than 150Ω · F  The measured and observed charac specifications in the following table.  No marking defects	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.  R9: 0.075max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 45 40 35 30 25 10 15 10 -5 -10 Apply the rat at 85±3°C ar Remove and	own below, 10 2 hours at roor  Humidity 90~98%  1 1 2 3 4 5 6 11  ed voltage and d 80 to 85% h d set for 24±2 l	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 90~98%  One cycle 24hours  The second of t	neasure. Humidity $80 \sim 98\%$ Humidity $90 \sim 9$
6	Biased Humidi	Capacitance Change Q/D.F.  I.R.  Appearance Capacitance	No marking defects $ \begin{tabular}{lll} Within $\pm 3.0\%$ or $\pm 0.30pF$ & (Whichever is larger) & 30pFmin.: $Q \ge 350$ & 10pF and over, $30pF$ and below: $Q \ge 275+5C/2$ & 10pFmax.: $Q \ge 200+10C$ & C: Nominal Capacitance(pF) & More than $10,000M\Omega$ or $500\Omega$ \cdot F$ & (Whichever is smaller) & R9: More than $150\Omega$ \cdot F$ & The measured and observed charac specifications in the following table. No marking defects & Within $\pm 3.0\%$ or $\pm 0.30pF$ & $\pm 0.30pF$$	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.  R9: 0.075max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 45 40 35 30 25 10 15 10 -5 -10 Apply the rat at 85±3°C ar Remove and	own below, 10 2 hours at roor  Humidity 90~98%  1 1 2 3 4 5 6 11  ed voltage and d 80 to 85% h d set for 24±2 l	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 10 2 c	neasure. Humidity $80 \sim 98\%$ Humidity $90 \sim 9$
6	Biased Humidi	Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Change	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≥350  10pF and over, 30pF and below: Q≥275+5C/2  10pFmax.: Q≥200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω ·F (Whichever is smaller)  R9: More than 150Ω ·F  The measured and observed charac specifications in the following table.  No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.  W.V.: 16V/10V: 0.05 max.  R9: 0.075max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 45 40 35 30 25 10 15 10 -5 -10 Apply the rat at 85±3°C ar Remove and	own below, 10 2 hours at roor  Humidity 90~98%  1 1 2 3 4 5 6 11  ed voltage and d 80 to 85% h d set for 24±2 l	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 10 2 c	neasure. Humidity $80 \sim 98\%$ Humidity $90 \sim 9$
6	Biased Humidi	Capacitance Change Q/D.F.  I.R.  Appearance Capacitance	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≥350  10pF and over, 30pF and below: Q≥275+5C/2  10pFmax.: Q≥200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω · F (Whichever is smaller)  R9: More than 150Ω · F  The measured and observed charac specifications in the following table.  No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pF and over: Q≥200	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 45 40 35 30 25 10 15 10 -5 -10 Apply the rat at 85±3°C ar Remove and	own below, 10 2 hours at roor  Humidity 90~98%  1 1 2 3 4 5 6 11  ed voltage and d 80 to 85% h d set for 24±2 l	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 10 2 c	neasure. Humidity $80 \sim 98\%$ Humidity $90 \sim 9$
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6	Biased Humidi	Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Change Q/D.F.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≥350  10pF and over, 30pF and below: Q≥275+5C/2  10pFmax.: Q≥200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω •F (Whichever is smaller)  R9: More than 150Ω •F  The measured and observed charac specifications in the following table.  No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pF and over: Q≥200  30pF and below: Q≥100+10C/3 C: Nominal Capacitance(pF)	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 45 40 35 30 25 10 15 10 -5 -10 Apply the rat at 85±3°C ar Remove and	own below, 10 2 hours at roor  Humidity 90~98%  1 1 2 3 4 5 6 :  ed voltage and d 80 to 85% h d set for 24±2 l	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 10 2 c	neasure. Humidity $80 \sim 98\%$ Humidity $90 \sim 9$
6	Biased Humidi	Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Change	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≥350  10pF and over, 30pF and below: Q≥275+5C/2  10pFmax.: Q≥200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω · F (Whichever is smaller)  R9: More than 150Ω · F  The measured and observed charac specifications in the following table.  No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pF and over: Q≥200  30pF and below: Q≥100+10C/3 C: Nominal Capacitance(pF)  More than 1,000MΩ or 50Ω · F	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. R9: 0.075max.  teristics should satisfy the  R7/L8/R9: Within ±12.5%  R7/L8 W.V.: 25Vmin.: 0.035 max. W.V.: 16V/10V: 0.05 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 45 40 35 30 25 10 15 10 -5 -10 Apply the rat at 85±3°C ar Remove and	own below, 10 2 hours at roor  Humidity 90~98%  1 1 2 3 4 5 6 :  ed voltage and d 80 to 85% h d set for 24±2 l	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 10 2 c	neasure. Humidity $80 \sim 98\%$ Humidity $90 \sim 9$
3	Biased Humidi	Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Change Q/D.F.	No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pFmin.: Q≥350  10pF and over, 30pF and below: Q≥275+5C/2  10pFmax.: Q≥200+10C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω •F (Whichever is smaller)  R9: More than 150Ω •F  The measured and observed charac specifications in the following table.  No marking defects  Within ±3.0% or ±0.30pF (Whichever is larger)  30pF and over: Q≥200  30pF and below: Q≥100+10C/3 C: Nominal Capacitance(pF)	R7/L8/R9: Within ±12.5%  R7/L8: W.V.: 25Vmin.: 0.03 max. W.V.: 16V/10V: 0.05 max. R9: 0.075max.  teristics should satisfy the  R7/L8/R9: Within ±12.5%  R7/L8 W.V.: 25Vmin.: 0.035 max. W.V.: 16V/10V: 0.05 max.	treatment sh Set for 24±:  Temperature (°C) 70 65 60 45 40 35 30 25 10 15 10 -5 -10 Apply the rat at 85±3°C ar Remove and	own below, 10 2 hours at roor  Humidity 90~98%  1 1 2 3 4 5 6 :  ed voltage and d 80 to 85% h d set for 24±2 l	Oconsecutive times.  In temperature, then in Humidity 80~98% Humidity 90~98% Humidity 10 2 c	neasure. Humidity $80 \sim 98\%$ Humidity $90 \sim 9$

- 1			Speci	fication.		
No	AEC-Q200	Test Item	Temperature Compensating Type	High Dielectric Type	AEC-Q200 Test Method	
7	Operational Life		The measured and observed chara- specifications in the following table	•	Apply 200% of the rated voltage for 1000 $\pm$ 12 hours at 125 $\pm$ 3°C(for $\Delta$ C/R7), 150 $\pm$ 3°C(for 5G/L8/R9).	
ļ		Appearance	No marking defects	T	Set for 24±2 hours at room temperature, then measure.	
ļ		Capacitance	Within ±3.0% or ±0.30pF	R7/L8/R9: Within ±12.5%	The charge/discharge current is less than 50mA.	
		Change	(Whichever is larger)	57/10 14/1/ 05/1/ 1 0.005	4	
		Q/D.F.	30pFmin. : Q≧350	R7/L8: W.V.: 25Vmin.: 0.035 max. (GCM155R71H 562-223: 0.05max)	Initial measurement for high dielectric constant type.	
			10pF and over, 30pF and below: Q≧275+5C/2	W.V.: 16V/10V : 0.05 max.	Apply 200% of the rated DC voltage for one hour at the maximun	
			Q≦275+5C/2 10pFmax.: Q ≧200+10C	R9 : 0.075max.	operating temperature ±3°C. Remove and set for 24±2 hours at room temperature. Perform initial measurement.	
			C: Nominal Capacitance(pF)	K9 . 0.075max.	noom temperature. Perronn mitar measurement.	
		I.R.	More than 1,000M $\Omega$ or 50 $\Omega$ •F (Whichever is smaller)			
3	External Visual		No defects or abnormalities		Visual inspection	
)	Phisical Dimen	sion	Within the specified dimensions		Using calipers	
0	Resistance to	Appearance	No marking defects		Per MIL-STD-202 Method 215	
ļ	Solvents	Capacitance	Within the specified tolerance		Solvent 1 : 1 part (by volume) of isopropyl alcohol	
		Change			3 parts (by volume) of mineral spirits	
		Q/D.F.	30pFmin. : Q≧1000	R7/L8 : W.V.: 25Vmin.: 0.025 max.	Solvent 2 : Terpene defluxer	
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.035 max.	Solvent 3 : 42 parts (by volume) of water	
			·			
			C: Nominal Capacitance(pF)	R9 : 0.05max.	1part (by volume) of propylene glycol monomethylether	
					1 part (by volume) of monoethanolomine	
ļ		I.R.	More than 10,000M $\Omega$ or 500 $\Omega$ •F			
			(Whichever is smaller)			
1	Mechanical	Appearance	No marking defects		Three shocks in each direction should be applied along 3 mutually	
•	Shock	Capacitance	Within the specified tolerance		perpendicular axes of the test specimen (18 shocks).	
ļ	SHOCK	· ·	Within the specified tolerance			
ļ		Change	00.5.0.0.0	D7/10 - W// - 05// 0 005	The specified test pulse should be Half-sine and should have a	
		Q/D.F.	30pFmin. : Q≧1000	R7/L8 : W.V.: 25Vmin.: 0.025 max.	duration :0.5ms, peak value:1500g and velocity change: 4.7m/s.	
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.035 max.		
			C: Nominal Capacitance(pF)	R9 : 0.05max.		
		I.R.	More than $10,000M\Omega$ or $500\Omega \cdot F$			
		I.R.	More than 10,000M $\Omega$ or 500 $\Omega$ •F (Whichever is smaller)			
2	Vibration	I.R. Appearance	·		Solder the capacitor to the test jig (glass epoxy board) in the same	
2	Vibration		(Whichever is smaller)		Solder the capacitor to the test jig (glass epoxy board) in the same manner and under the same conditions as (19). The capacitor	
2	Vibration	Appearance	(Whichever is smaller)  No defects or abnormalities			
12	Vibration	Appearance Capacitance	(Whichever is smaller)  No defects or abnormalities	R7/L8 : W.V.: 25Vmin.: 0.025 max.	manner and under the same conditions as (19). The capacitor	
2	Vibration	Appearance Capacitance Change	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance	R7/L8 : W.V.: 25Vmin.: 0.025 max. W.V.: 16V/10V : 0.035 max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total	
2	Vibration	Appearance Capacitance Change	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000  30pFmax.: Q≧400+20C	W.V.: 16V/10V : 0.035 max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from	
2	Vibration	Appearance Capacitance Change	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin. : Q≧1000		manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in	
12	Vibration	Appearance Capacitance Change Q/D.F.	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≥1000  30pFmax.: Q≥400+20C  C: Nominal Capacitance(pF)	W.V.: 16V/10V : 0.035 max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12	
2	Vibration	Appearance Capacitance Change	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≥1000 30pFmax.: Q≥400+20C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω · F	W.V.: 16V/10V : 0.035 max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in	
2	Vibration	Appearance Capacitance Change Q/D.F.	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≥1000  30pFmax.: Q≥400+20C  C: Nominal Capacitance(pF)	W.V.: 16V/10V : 0.035 max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12	
	Vibration  Resistance to	Appearance Capacitance Change Q/D.F.	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≥1000 30pFmax.: Q≥400+20C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω · F	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12	
		Appearance Capacitance Change Q/D.F.	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q≥400+20C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω • F (Whichever is smaller)	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12 items in each 3 mutually perpendicular directions (total of 36 times).	
	Resistance to	Appearance Capacitance Change Q/D.F.	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q≥400+20C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω • F (Whichever is smaller)	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12 items in each 3 mutually perpendicular directions (total of 36 times).	
	Resistance to	Appearance Capacitance Change Q/D.F.	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q≥400+20C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω • F (Whichever is smaller)  The measured and observed chars specifications in the following tables	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12 items in each 3 mutually perpendicular directions (total of 36 times). Immerse the capacitor in a eutectic solder solution at $260\pm5^{\circ}\text{C}$ for $10\pm1$ seconds. Set at room temperature for $24\pm2$ hours, then	
	Resistance to	Appearance Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Change	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q≥400+20C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω • F (Whichever is smaller)  The measured and observed charaspecifications in the following table No marking defects	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12 items in each 3 mutually perpendicular directions (total of 36 times). Immerse the capacitor in a eutectic solder solution at $260\pm5^{\circ}\text{C}$ for $10\pm1$ seconds. Set at room temperature for $24\pm2$ hours, then	
	Resistance to	Appearance Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Capacitance	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000  30pFmax.: Q≥400+20C  C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω • F  (Whichever is smaller)  The measured and observed charaspecifications in the following table No marking defects  Within the specified tolerance  30pFmin.: Q≥1000	W.V.: 16V/10V: 0.035 max. R9: 0.05max.  acteristics should satisfy the state of the	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12 items in each 3 mutually perpendicular directions (total of 36 times).  Immerse the capacitor in a eutectic solder solution at 260±5°C for 10±1 seconds. Set at room temperature for 24±2 hours, then measure.  Initial measurement for high dielectric constant type  Perform a heat treatment at 150+0/-10 °C for one hour and then set	
	Resistance to	Appearance Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Change	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q≥400+20C C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω • F (Whichever is smaller)  The measured and observed charaspecifications in the following table No marking defects  Within the specified tolerance	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.  acteristics should satisfy the	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12 items in each 3 mutually perpendicular directions (total of 36 times). Immerse the capacitor in a eutectic solder solution at $260\pm5^{\circ}\mathrm{C}$ for $10\pm1$ seconds. Set at room temperature for $24\pm2$ hours, then measure.	
	Resistance to	Appearance Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Change	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q≥400+20C  C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω • F (Whichever is smaller)  The measured and observed charaspecifications in the following table No marking defects  Within the specified tolerance  30pFmin.: Q≥1000 30pFmax.: Q≥400+20C	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.  acteristics should satisfy the  R7/L8 : W.V.: 25Vmin.: 0.025 max. W.V.: 16V/10V : 0.035 max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12 items in each 3 mutually perpendicular directions (total of 36 times).  Immerse the capacitor in a eutectic solder solution at 260±5°C for 10±1 seconds. Set at room temperature for 24±2 hours, then measure.  Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set for 24±2 hours at room temperature.	
	Resistance to	Appearance Capacitance Change Q/D.F.  I.R.  Appearance Capacitance Change Q/D.F.	(Whichever is smaller)  No defects or abnormalities  Within the specified tolerance  30pFmin.: Q≧1000  30pFmax.: Q≧400+20C  C: Nominal Capacitance(pF)  More than 10,000MΩ or 500Ω •F  (Whichever is smaller)  The measured and observed charaspecifications in the following table  No marking defects  Within the specified tolerance  30pFmin.: Q≥1000  30pFmax.: Q≥400+20C  C: Nominal Capacitance(pF)	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.  acteristics should satisfy the  R7/L8 : W.V.: 25Vmin.: 0.025 max. W.V.: 16V/10V : 0.035 max.	manner and under the same conditions as (19). The capacitor should be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 2000Hz. The frequency range, from 10 to 2000Hz and return to 10Hz, should be traversed in approximately 20 minutes. This motion should be applied for 12 items in each 3 mutually perpendicular directions (total of 36 times).  Immerse the capacitor in a eutectic solder solution at 260±5°C for 10±1 seconds. Set at room temperature for 24±2 hours, then measure.  Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set for 24±2 hours at room temperature.	

			Speci	ification.					
No	AEC-Q	200 Test Item	Temperature Compensating Type	High Dielectric Type			AEC-Q200 Tes	st Method	
14 T	hermal Sh	nock	The measured and observed charact specifications in the following table.	eristics should satisfy the	Fix the capacitor to the supporting jig in the same manner and under the same conditions as (19). Perform the 300 cycles according to the two heat treatments listed in the following table(Maximum				
		Appearance	No marking defects						
		Capacitance	Within ±2.5% or ±0.25pF	R7/L8/R9: Within ±10.0%	transfe	er time is 20 se	conds). Set for 24±	2 hours at room	
		Change	(Whichever is larger)		temper	rature, then me	ture, then measure		
		Q/D.F.	30pFmin. : Q≧1000	R7/L8 : W.V.: 25Vmin.: 0.025 max.*	<b>1</b>	Step	1	2	
			30pFmax.: Q ≧400+20C	*0.05max:GCM188R71E/1H563 to 104		Осер	'		
			· ·	W.V.: 16V/10V : 0.035 max.	Temp.(°C) -55+0/-3 125+3/-0(forΔC/R7) 150+3/-0 (for 5G/L8				
			C: Nominal Capacitance(pF)			Time		10010/ 0 (101 00/20/10/	
				R9: 0.05max		Time (min.)	15±3	15±3	
		I.R.	More than 10,000MΩ or 500Ω • F						
			(Whichever is smaller)		Perforr for 24±	m a heat treatr	om temperature.	constant type C for one hour and then set	
5 F	SD	Appearance	No marking defects		Per AF	C-Q200-002			
٦	.00	Capacitance	Within the specified tolerance		-	.O Q200 002			
		Capacitance	within the specified tolerance						
		Q/D.F.	30pFmin. : Q≧1000	R7/L8 : W.V.: 25Vmin.: 0.025 max.	+				
		J	30pFmin. : Q ≥ 1000 30pFmax.: Q ≥ 400+20C						
			'	W.V.: 16V/10V :0.035 max.					
			C: Nominal Capacitance(pF)	R9: 0.05max.					
		I D							
		I.R.	More than 10,000MΩ or 500Ω•F						
Solderability			(Whichever is smaller)  95% of the terminations is to be solded	and accepts and a setting continuously.	( ) 5	1		eheating, immerse the	
					eute	ectic solder sol	in weight propotion) lution for 5+0/-0.5 se	econds at 235±5°C.	
					Afte etha prop second (c) sho Afte etha	anol(JIS-K-810 potion). Immer onds at 235±5 auld be placed or preheating, i anol(JIS-K-810	immerse the capacit of other	or in a solution of 5902) (25% rosin in weight solution for 5+0/-0.5 8 hours±15 minutes. or in a solution of 5902) (25% rosin in weight	
					(c) sho Afte	anol(JIS-K-810 potion). Immer onds at 235±5 auld be placed or preheating, i anol(JIS-K-810	immerse the capacit ()1) and rosin (JIS-K- se in eutectic solder (°C.) into steam aging for immerse the capacit ()1) and rosin (JIS-K- se in eutectic solder	or in a solution of 5902) (25% rosin in weight solution for 5+0/-0.5 8 hours±15 minutes. or in a solution of 5902) (25% rosin in weight	
	Electrical	Appearance	No defects or abnormalities		After ethat prop second (c) sho After ethat prop second Visual	anol(JIS-K-810 potion). Immer onds at 235±5 and be placed or preheating, i anol(JIS-K-810 potion). Immer onds at 260±5' inspection.	immerse the capacit of and rosin (JIS-K-se in eutectic solder of C.  into steam aging for immerse the capacit of and rosin (JIS-K-se in eutectic solder of C.	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5	
c	Chatacteri-	Capacitance	No defects or abnormalities Within the specified tolerance		After ethat prop second (c) sho After ethat prop second Visual The car	anol(JIS-K-810 potion). Immer onds at 235±5 puld be placed or preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection.	immerse the capacit (01) and rosin (JIS-K- se in eutectic solder (°C.) into steam aging for immerse the capacit (01) and rosin (JIS-K- se in eutectic solder (°C.) (0.F. should be meas	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the	
c		Capacitance Change	Within the specified tolerance		After ethat prop second (c) sho After ethat prop second Visual The car	anol(JIS-K-810 potion). Immer onds at 235±5 puld be placed or preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection.	immerse the capacit of and rosin (JIS-K-se in eutectic solder of C.  into steam aging for immerse the capacit of and rosin (JIS-K-se in eutectic solder of C.	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the	
C	Chatacteri-	Capacitance		R7/L8 : W.V.: 25Vmin.: 0.025 max.	After ethat prop second (c) sho After ethat prop second Visual The car	anol(JIS-K-810 potion). Immer onds at 235±5 puld be placed or preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection.	immerse the capacit (21) and rosin (JIS-K- se in eutectic solder (3°C.) into steam aging for immerse the capacit (21) and rosin (JIS-K- se in eutectic solder (3°C.) (3°C.) (4.5) (5.5) (6.5) (7.5) (7.5) (8	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the	
C	Chatacteri-	Capacitance Change	Within the specified tolerance	R7/L8: W.V.: 25Vmin.: 0.025 max. W.V.: 16V/10V: 0.035 max.	After ethat prop second (c) sho After ethat prop second Visual The car	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed or preheating, i anol(JIS-K-810 potion). Immer onds at 260±5' inspection. pacitance/Q/C ncy and voltag  Char.	immerse the capacit (01) and rosin (JIS-K- se in eutectic solder (°C.) into steam aging for immerse the capacit (01) and rosin (JIS-K- se in eutectic solder (°C.) (0.F. should be meas	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the c.  A C,5G (more than 1000pF)	
C	Chatacteri-	Capacitance Change	Within the specified tolerance  30pFmin. : Q≧1000		(c) sho After ethat prop seco  (c) sho After ethat prop seco  Visual The ca frequer	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5' inspection. inspection. pacitance/Q/E ncy and voltag Char. Item	immerse the capacit of an armonic of the capacit of	or in a solution of 6:5902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 6:5902) (25% rosin in weight solution for 120±5  ured at 25°C at the example of $\frac{\Delta C.5G}{R7.R9.L8(C \le 10  \mu  F)}$	
C	Chatacteri-	Capacitance Change	Within the specified tolerance  30pFmin. : Q≥1000  30pFmax.: Q≥400+20C	W.V.: 16V/10V : 0.035 max.	(c) sho After ethat prop secon  (c) sho After ethat prop secon  Visual The ca frequer	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed or preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. inspection. inspection. Char. Item Frequency	immerse the capacit of an armonic of an armonic of a capacit of a capa	or in a solution of 6.5902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 6.5902) (25% rosin in weight solution for 120±5  ured at 25°C at the expectation of 6.5902) ( $^{\Delta}C$ ,5 $^{\omega}C$ , at the $^{\omega}C$ , $^{\omega}C$	
C	Chatacteri-	Capacitance Change	Within the specified tolerance  30pFmin. : Q≥1000  30pFmax.: Q≥400+20C	W.V.: 16V/10V : 0.035 max.	(c) sho After ethat prop secon  (c) sho After ethat prop secon  Visual The ca frequer	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5' inspection. inspection. pacitance/Q/E ncy and voltag Char. Item	immerse the capacit of an armonic of the capacit of	or in a solution of 6:5902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 6:5902) (25% rosin in weight solution for 120±5  ured at 25°C at the expectation of 6:5902) (25% rosin in weight solution for 120±6) $\frac{\Delta C.5G}{R7.R9.L8(C \le 10  \mu  F)}$	
C	Chatacteri-	Capacitance Change Q/D.F.	Within the specified tolerance  30pFmin. : Q≧1000  30pFmax.: Q ≧400+20C  C: Nominal Capacitance(pF)	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.	(c) sho After ethat prop seco  (c) sho After ethat prop seco  Visual The ca frequer	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. inspection. inspection. Char. Item Frequency /oltage	immerse the capacit of and rosin (JIS-K-se in eutectic solder of an eutectic solder of a	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the 6. $\Delta C.5G$ (more than 1000pF) R7,R9,L8( $C \le 10 \mu F$ ) 1±0.1kHz 1±0.2Vrms	
C	Chatacteri-	Capacitance Change	Within the specified tolerance  30pFmin. : Q≥1000  30pFmax.: Q≥400+20C	W.V.: 16V/10V : 0.035 max.	(c) sho After ethat prop seco  (c) sho After ethat prop seco  Visual The ca frequer	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. inspection. pacitance/Q/D ncy and voltage Char. Item Frequency /oltage	immerse the capacit of and rosin (JIS-K-se in eutectic solder of an eutectic solder of a	or in a solution of 65902) (25% rosin in weight 5902) (25% rosin in weight 5002) (25% rosin in weight 75002) (25% rosin in weight 75% rosin in we	
C	Chatacteri-	Capacitance Change Q/D.F.	Within the specified tolerance  30pFmin. : Q≧1000  30pFmax.: Q ≧400+20C  C: Nominal Capacitance(pF)	W.V.: 16V/10V : 0.035 max. R9 : 0.05max.	(c) sho After ethat prop seco  (c) sho After ethat prop seco  Visual The ca frequer	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. inspection. pacitance/Q/D ncy and voltage Char. Item Frequency /oltage	immerse the capacit of and rosin (JIS-K-se in eutectic solder of an eutectic solder of a	or in a solution of 65902) (25% rosin in weight 5902) (25% rosin in weight 5002) (25% rosin in weight 5001) as solution of 55902) (25% rosin in weight 5002) (25% rosin in weight 5002) (25% cat the 5002) $\Delta C.5G$ (more than 1000pF) $R7.R9.L8(C \le 10  \mu F)$ $1\pm 0.1 kHz$ $1\pm 0.2 Vrms$	
C	Chatacteri-	Capacitance Change Q/D.F.	Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q ≧400+20C C: Nominal Capacitance(pF)  More than 100,000MΩ or 1000Ω•F	W.V.: 16V/10V : 0.035 max. R9 : 0.05max. More than 10,000M $\Omega$ or 500 $\Omega$ -F	(c) sho After ethat prop secci (c) sho After ethat prop secci Visual The ca frequer  The insexcect	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. inspection. pacitance/Q/D ncy and voltage  Char. Item Frequency /oltage	immerse the capacit of and rosin (JIS-K-se in eutectic solder of an eutectic solder of a	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the 8. $\frac{\Delta C,5G}{\text{(more than 1000pF)}}$ $\frac{A}{R7,R9,L8}(C \le 10 \mu\text{F})$ $1\pm 0.1\text{kHz}$ $1\pm 0.2\text{Vrms}$ sured with a DC voltage not 125°C (for $\Delta$ C/R7)/150°C	
C	Chatacteri-	Capacitance Change Q/D.F.	Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q ≧400+20C C: Nominal Capacitance(pF)  More than 100,000MΩ or 1000Ω•F	W.V.: 16V/10V : 0.035 max. R9 : 0.05max. More than 10,000M $\Omega$ or 500 $\Omega$ -F	(c) sho After ethat prop secci (c) sho After ethat prop secci Visual The ca frequer  The insexcect	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. inspection. pacitance/Q/D ncy and voltage  Char. Item Frequency /oltage	immerse the capacit of and rosin (JIS-K-se in eutectic solder of an eutectic solder of a	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the 8. $\frac{\Delta C,5G}{\text{(more than 1000pF)}}$ $\frac{A}{R7,R9,L8}(C \le 10 \mu\text{F})$ $1\pm 0.1\text{kHz}$ $1\pm 0.2\text{Vrms}$ sured with a DC voltage not 125°C (for $\Delta$ C/R7)/150°C	
c	Chatacteri-	Capacitance Change Q/D.F.	Within the specified tolerance  30pFmin.: Q≧1000 30pFmax.: Q ≧400+20C C: Nominal Capacitance(pF)  More than 100,000MΩ or 1000Ω•F (Whichever is smaller)	$W.V.: 16V/10V: 0.035 \ max.$ $R9: 0.05 max.$ $More \ than \ 10,000 M\Omega \ or \ 500 \Omega \cdot F$ $(Whichever \ is \ smaller)$	(c) sho After ethat prop secci (c) sho After ethat prop secci Visual The ca frequer  The insexcect	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. inspection. pacitance/Q/D ncy and voltage  Char. Item Frequency /oltage	immerse the capacit of and rosin (JIS-K-se in eutectic solder of an eutectic solder of a	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the 8. $\frac{\Delta C,5G}{\text{(more than 1000pF)}}$ $\frac{A}{R7,R9,L8}(C \le 10 \mu\text{F})$ $1\pm 0.1\text{kHz}$ $1\pm 0.2\text{Vrms}$ sured with a DC voltage not 125°C (for $\Delta$ C/R7)/150°C	
C	Chatacteri-	Capacitance Change Q/D.F.	Within the specified tolerance $30pFmin.: Q \geqq 1000 \\ 30pFmax.: Q \geqq 400+20C \\ C: Nominal Capacitance(pF)$ More than $1000000000000000000000000000000000000$	$W.V.: 16V/10V: 0.035 \ max.$ R9: $0.05max$ .   More than $10,000M\Omega$ or $500\Omega \cdot F$ (Whichever is smaller)   More than $1,000M\Omega$ or $10\Omega \cdot F$	(c) sho After ethat prop secci (c) sho After ethat prop secci Visual The ca frequer  The insexcect	anol(JIS-K-810 potion). Immer onds at 235±5 uld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. inspection. pacitance/Q/D ncy and voltage  Char. Item Frequency /oltage	immerse the capacit of and rosin (JIS-K-se in eutectic solder of an eutectic solder of a	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5  8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5  ured at 25°C at the 8. $\frac{\Delta C,5G}{\text{(more than 1000pF)}}$ $\frac{A}{R7,R9,L8}(C \le 10 \mu\text{F})$ $1\pm 0.1\text{kHz}$ $1\pm 0.2\text{Vrms}$ sured with a DC voltage not 125°C (for $\Delta$ C/R7)/150°C	
C	Chatacteri-	Capacitance Change Q/D.F.  I.R. 25°C  I.R. 125°C	Within the specified tolerance $30pFmin.: Q \geqq 1000 \\ 30pFmax.: Q \geqq 400+20C \\ C: Nominal Capacitance(pF)$ $More than 100,000M\Omega \text{ or } 1000\Omega \cdot F \\ (Whichever is smaller)$ $More than 10,000M\Omega \text{ or } 100\Omega \cdot F \\ (Whichever is smaller)$ $More than 10,000M\Omega \text{ or } 100\Omega \cdot F \\ (Whichever is smaller)$	$W.V.: 16V/10V: 0.035 \ max.$ R9: $0.05 max.$ More than $10,000 M\Omega$ or $500 \Omega \cdot F$ (Whichever is smaller)  More than $1,000 M\Omega$ or $10 \Omega \cdot F$ (Whichever is smaller)  More than $1,000 M\Omega$ or $10 \Omega \cdot F$	After ethal propries second (c) show the ethal prop	anol(JIS-K-810 potion). Immer onds at 235±5 puld be placed or preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. pacitance/Q/C incy and voltage  Char. Item Trequency //oltage sulation resistate ding the rated of G/L8/R9) within	immerse the capacit of and rosin (JIS-K-se in eutectic solder of c. into steam aging for immerse the capacit of and rosin (JIS-K-se in eutectic solder of c. of an eutecti	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5 8 hours±15 minutes. or in a solution of 65902) (25% rosin in weight solution for 120±5 $\frac{\Delta \text{C,5G}}{\text{(more than 1000pF)}}$ $\frac{\text{R7,R9,L8}(\text{C} \leq 10\mu\text{F})}{\text{1\pm}0.1\text{kHz}}$ $\frac{1}{\text{1\pm}0.2\text{Vrms}}$ sured with a DC voltage not 125°C (for $\Delta$ C/R7)/ 150°C ing.	
C	Chatacteri-	Capacitance Change Q/D.F.  I.R. 25°C  I.R. 150°C  Dielectric	Within the specified tolerance $30pFmin.: Q \geqq 1000 \\ 30pFmax.: Q \geqq 400+20C \\ C: Nominal Capacitance(pF)$ More than $100,000M\Omega$ or $1000\Omega \cdot F$ (Whichever is smaller) $More than 10,000M\Omega or 100\Omega \cdot F (Whichever is smaller) More than 10,000M\Omega or 100\Omega \cdot F (Whichever is smaller)$	$W.V.: 16V/10V: 0.035 \ max.$ R9: $0.05 max.$ More than $10,000 M\Omega$ or $500 \Omega \cdot F$ (Whichever is smaller)  More than $1,000 M\Omega$ or $10 \Omega \cdot F$ (Whichever is smaller)  More than $1,000 M\Omega$ or $10 \Omega \cdot F$	After ethal propries section (c) show the ethal propries section (	anol(JIS-K-810 potion). Immer onds at 235±5 puld be placed or preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. pacitance/Q/C incy and voltage  Char. Item Trequency //oltage  sulation resistating the rated of G/L8/R9) within ure should be	immerse the capacit of and rosin (JIS-K-se in eutectic solder oc. into steam aging for immerse the capacit of and rosin (JIS-K-se in eutectic solder oc. oc. oc. into steam aging for immerse the capacit of and rosin (JIS-K-se in eutectic solder oc. oc. oc. oc. into steam aging for immerse the capacit of an eutectic solder oc.	or in a solution of 65902) (25% rosin in weight solution for 5+0/-0.5 8 hours±15 minutes. or in a solution of 5902) (25% rosin in weight solution for 120±5 $\frac{\Delta \text{ C,5G}}{\text{(more than 1000pF)}}$ $\frac{\text{R7,R9,L8}(\text{C} \le 10  \mu\text{F})}{\text{1\pm}0.1\text{kHz}}$ $\frac{1}{\text{1\pm}0.2\text{Vrms}}$ surred with a DC voltage not 125°C (for $\Delta$ C/R7)/ 150°C ing.	
C	Chatacteri-	Capacitance Change Q/D.F.  I.R. 25°C  I.R. 125°C	Within the specified tolerance $30pFmin.: Q \geqq 1000 \\ 30pFmax.: Q \geqq 400+20C \\ C: Nominal Capacitance(pF)$ $More than 100,000M\Omega \text{ or } 1000\Omega \cdot F \\ (Whichever is smaller)$ $More than 10,000M\Omega \text{ or } 100\Omega \cdot F \\ (Whichever is smaller)$ $More than 10,000M\Omega \text{ or } 100\Omega \cdot F \\ (Whichever is smaller)$	$W.V.: 16V/10V: 0.035 \ max.$ R9: $0.05 max.$ More than $10,000 M\Omega$ or $500 \Omega \cdot F$ (Whichever is smaller)  More than $1,000 M\Omega$ or $10 \Omega \cdot F$ (Whichever is smaller)  More than $1,000 M\Omega$ or $10 \Omega \cdot F$	After ethal propries second (c) show the ethal prop	anol(JIS-K-810 potion). Immer onds at 235±5 puld be placed er preheating, i anol(JIS-K-810 potion). Immer onds at 260±5 inspection. pacitance/Q/C incy and voltage  Char. Item Trequency /oltage sulation resistating the rated of G/L8/R9) within ure should be diselected between the	immerse the capacit of and rosin (JIS-K-se in eutectic solder oc. into steam aging for immerse the capacit of and rosin (JIS-K-se in eutectic solder oc. oc. oc. into steam aging for immerse the capacit of and rosin (JIS-K-se in eutectic solder oc. oc. oc. oc. into steam aging for immerse the capacit of an eutectic solder oc.	or in a solution of $.5902$ ) (25% rosin in weight solution for $5+0/-0.5$ 8 hours±15 minutes. or in a solution of $.5902$ ) (25% rosin in weight solution for $120\pm5$ ured at $25^{\circ}$ C at the $$ $\Delta C,5G$ (more than $1000\text{pF}$ ) $R7,R9,L8(C \le 10\mu\text{F})$ $1\pm0.1\text{kHz}$ $1\pm0.2\text{Vrms}$ sured with a DC voltage not $125^{\circ}$ C (for $\Delta$ C/R7)/ $150^{\circ}$ C ing.	

			Sp	ecification.					
No	AEC-Q200	Test Item	Temperature Compensating Type	High Dielectric Type	AEC-Q200 Test Method				
18	Board Flex	Appearance	No marking defects		Solder the capacitor on the test jig (glass epoxy board) shown in Fig1 using a eutectic solder. Then apply a force in the direction shown in Fig 2 for 5±1sec. The soldering should be done by the reflow method and should be conducted with care so that the				
		Capacitance	Within ±5.0% or ±0.5pF	R7/L8/R9: Within ±10.0%	soldering is uniform and free of defects such as heat shock.				
		Change	(Whichever is larger)		Type a b c				
		Q/D.F.	30pFmin. : Q≧1000	R7/L8: W.V.: 25Vmin.: 0.025 max.	GCM03 0.3 0.9 0.3				
			30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.035max.	GCM15 0.5 1.5 0.6 GCM18 0.6 2.2 0.9				
			C: Nominal Capacitance(pF)	R9 : 0.05max.	GCM21 0.8 3.0 1.3				
		I.R.	More than 10,000MΩ or 500	0 ·F	GCM31 2. 0 4. 4 1. 7 GCM32 2. 0 4. 4 2. 6				
			(Whichever is smaller)	52 I	(in mm)				
			b   b   c   c   c   c   c   c   c   c		Pressurizing speed:1. Omm/s Pressurize  R44  Pressurizing speed:1. Omm/s Pressurize  Flexure: ≤2 (High Dielectric Type) Flexure: ≤3 (Temperature				
				(GCM03/15:0.8mm	Fig. 2				
19	Terminal Strength	Appearance	No marking defects		Solder the capacitor to the test jig (glass epoxy board) shown in Fig.3 using a eutectic solder. Then apply *18N force in parallel with				
		Capacitance	Within specified tolerance		the test jig for 60sec.				
		Change Q/D.F.	30pFmin. : Q≧1000	R7/L8 : W.V.: 25Vmin.: 0.025 max.	The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is				
		Q.2	30pFmax.: Q ≧400+20C	W.V.: 16V/10V : 0.035max.	uniform and gree of defects such as heat shock				
			C: Nominal Capacitance(pF)	R9 : 0.05max.	*2N(GCM03/15)				
		I.R.	More than 10,000M $\Omega$ or 500 (Whichever is smaller)	Ω·F	Type a b c GCM03 0.3 0.9 0.3 GCM15 0.4 1.5 0.5 GCM18 1.0 3.0 1.2 GGM21 1.2 4.0 1.65 GCM31 2.2 5.0 2.0 GCM32 2.2 5.0 2.9  (in mm)				
					t: 1.6mm (GCM03/15: 0.8mm)  Solder resist  Baked electrode or Copper foil				
					Fig. 3				
20	Beam Load Test		Destruction value should be exceed following one.  < Chip L dimension: 2.5mm max. >  Chip thickness > 0.5mm rank: 20N  Chip thickness ≤ 0.5mm rank: 8N  < Chip L dimension: 3.2mm max. >  Chip thickness < 1.25mm rank: 15N  Chip thickness ≥ 1.25mm rank: 54.5N		Place the capacitor in the beam load fixture as Fig 4.  Apply a force.  < Chip Length: 2.5mm max. >  Iron Board				
					< Chip Length : 3.2mm min. >				
					O.GL				
					Fig.4				
					Speed supplied the Stress Load: *0.5mm / sec. *GCM03: 0.1mm/sec.				

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JEMCGS-0363S

			Specif	ication.			
No	AEC-Q2	00 Test Item	Temperature Compensating Type	High Dielectric Type	AEC-Q200 Test Method		
21	Capacitance Temperature Characteristics	Capacitance Change	Within the specified tolerance. (Table A)	R7: Within $\pm 15\%$ (-55°C to +125°C) L8: Within $\pm 15\%$ (-55°C to +125°C) Within +15/-40% (+125°C to +150°C) R9: Within $\pm 15\%$	The capacitance change should be measured after 5 min. at each specified temperature stage.  (1)Temperature Compensating Type The temperature coefficient is determind using the capacitance measured in step 3 as a reference. When cycling the temperature sequentially from step1 through 5 (Δ C: +25°C to +125°C, 5G:+25°C to +150°C other temp. coeffs::+25°C to +85°C) the		
				(-55°C to +150°C)	capacitance should be within the specified tolerance for the temperature coefficient and capacitance change as Table A-1. The capacitance drift is caluculated by dividing the differences between the maximum and minimum measured values in the step		
		Temperature Coefficent	Within the specified tolerance. (Table A)		1,3 and 5 by the cap value in step 3.    Step		
		Capacitance Drift	Within ±0.2% or ±0.05 pF (Whichever is larger.)		4 125±3(for ΔC/R7), 150±3(for 5G/R9/L8),85±3(for other TC)  5 25±2  (2) High Dielectric Constant Type The ranges of capacitance change compared with the above 25°C value over the temperature ranges shown in the table should be within the specified ranges.  Initial measurement for high dielectric constant type. Perform a heat treatment at 150+0/-10°C for one hour and then set for 24±2 hours at room temperature. Perform the initial measurement.		

#### Table A

	Naminal Values		Capa	citance Char	nge from 25°0	C (%)					
Char.	Nominal Values	-5	55	-30 -10		0					
	(ppm/°C)	Max.	Min.	Max.	Min.	Max.	10 Min.				
5C/5G	0± 30	0.58	-0.24	0.40	-0.17	0.25	-0.11				

Note 1: Nominal values denote the temperature coefficient within a range of 25°C to 125°C(for  $\Delta$ C)/ 150°C(for 5G)/85°C(for other TC).

# 1.Tape Carrier Packaging(Packaging Code:D/E/W/F/L/J/K) 1.1 Minimum Quantity(pcs./reel)

			φ180mm reel		φ330mm reel		
T	ype	Paper	· Tape	Plastic Tape	Paper Tape	Plastic Tape	
		Code:D/E	Code:W	Code:L	Code:J/ F	Code:K	
GC□03		15000(W8P2)	30000(W8P1)		50000(W8P2)		
GC□15		10000(W8P2)	20000(W8P1)		50000(W8P2)		
GC□18		4000			10000		
	6	4000			10000		
GC□21	9	4000			10000		
	В			3000		10000	
	6	4000			10000		
GC□31	9	4000			10000		
ВСПЗТ	M			3000		10000	
	С			2000		6000	
	9	4000			10000		
GC□32	М			3000		10000	
GCL 32	Ν			2000		8000	
	R/D/E			1000		4000	
	М			1000		5000	
GC□43	N/R			1000		4000	
	Е			500		2000	
GC□55	М			1000		5000	
GCL33	N/R			1000		4000	

# 1.2 Dimensions of Tape (1)GC□03/15(W8P2 CODE:D/E/J/F)

(in:mm)



Code	GC□03	GC□15	
A *3	0.37	0.65	
B *3	0.67	1.15	*3 Nominal value
t	0.5 max.	0.8 max.	

# (2)GC□03/15(W8P1 CODE:W)

(in:mm)



Code	GC 🗆 03	GC□15
Α*	0.37	0.65
B *	0.67	1.15
t	0.5 max.	0.8 max.
	A * B *	A * 0.37 B * 0.67

\* Nominal value



Code	GC□18	GC□21	GC□31	GC□32
Α	1.05±0.1	1.55±0.15	2.0±0.2	2.8±0.2
В	1.85±0.1	2.3±0.15	3.6±0.2	3.6±0.2



(5)GC□43/55		(in:mm)
	3±0.1	*: 2.0±0.1
	*1	*1 2.5 max. (T≦1.8mm)

Code	GC□43	GC□55	
A *2	3.6	5.2	*2 Nominal value
B *2	4.9	6.1	

W

W<sub>1</sub>

Fig.1 Package Chips (in:mm)

Fig.2 Dimensions of Reel

Fig.3 Taping Diagram



- 1.3 Tapes for capacitors are wound clockwise shown in Fig.3.

  (The sprocket holes are to the right as the tape is pulled toward the user.)
- 1.4 Part of the leader and part of the vacant section are attached as follows.



- 1.5 Accumulate pitch : 10 of sprocket holes pitch =  $40\pm0.3$ mm
- 1.6 Chip in the tape is enclosed by top tape and bottom tape as shown in Fig.1.
- 1.7 The top tape and base tape are not attached at the end of the tape for a minimum of 5 pitches.
- 1.8 There are no jointing for top tape and bottom tape.
- 1.9 There are no fuzz in the cavity.
- 1.10 Break down force of top tape : 5N min.
  Break down force of bottom tape : 5N min. (Only a bottom tape existence)
- 1.11 Reel is made by resin and appeaser and dimension is shown in Fig 2. There are possibly to change the material and dimension due to some impairment.
- 1.12 Peeling off force: 0.1N to 0.6N\* in the direction as shown below.
  - \* GC□03:0.05N~0.5N

    165~180°

    Top tape
- 1.13 Label that show the customer parts number, our parts number, our company name, inspection number and quantity, will be put in outside of reel.

#### Limitation of use

Please contact our sales representatives or product engineers before using our products for the applications listed below which require of our products for other applications than specified in this product.

- ①Aircraft equipment ②Aerospace equipment ③Undersea equipment ④Power plant control equipment
- ⑤Medical equipment ⑥Transportation equipment(vehicles,trains,ships,etc.) ⑦Traffic signal equipment
- ®Disaster prevention / crime prevention equipment
  9Data-processing equipment
- (II) Application of similar complexity and/or requirements to the applications listed in the above

#### ■ Fail-safe

Be sure to provide an appropriate fail-safe function on your product to prevent a second damage that may be caused by the abnormal function or the failure of our product.

#### ■ Storage and Operation condition

- 1. The performance of chip monolithic ceramic capacitors may be affected by the storage conditions.
- 1-1. Store capacitors in the following conditions: Temperature of +5°C to +40°C and a Relative Humidity of 20% to 70%.
- (1) Sunlight, dust, rapid temperature changes, corrosive gas atmosphere or high temperature and humidity conditions during storage may affect the solderability and the packaging performance. Please use product within six months of receipt.
- (2) Please confirm solderability before using after six months. Store the capacitors without opening the original bag. Even if the storage period is short, do not exceed the specified atmospheric conditions.
- 1-2. Corrosive gas can react with the termination (external) electrodes or lead wires of capacitors, and result in poor solderability. Do not store the capacitors in an atmosphere consisting of corrosive gas (e.g., hydrogen sulfide, sulfur dioxide, chlorine, ammonia gas etc.).
- 1-3. Due to moisture condensation caused by rapid humidity changes, or the photochemical change caused by direct sunlight on the terminal electrodes and/or the resin/epoxy coatings, the solderability and electrical performance may deteriorate. Do not store capacitors under direct sunlight or in high huimidity conditions

## ■Rating

#### **1.Temperature Dependent Characteristics**

- 1. The electrical characteristics of the capacitor can change with temperature.
- 1-1. For capacitors having larger temperature dependency, the capacitance may change with temperature changes. The following actions are recommended in order to insure suitable capacitance values.
  - (1) Select a suitable capacitance for the operating temperature range.
- (2) The capacitance may change within the rated temperature.
  - When you use a high dielectric constant type capacitors in a circuit that needs a tight (narrow) capacitance tolerance.

Example: a time constant circuit., please carefully consider the characteristics of these capacitors, such as their aging, voltage, and temperature characteristics.

And check capacitors using your actual appliances at the intended environment and operating conditions.

☐ Typical temperature characteristics Char.R6 (X5R)







☐ Typical temperature characteristics Char.F5 (Y5V)



#### 2.Measurement of Capacitance

- 1. Measure capacitance with the voltage and the frequency specified in the product specifications.
- 1-1. The output voltage of the measuring equipment may decrease when capacitance is high occasionally. Please confirm whether a prescribed measured voltage is impressed to the capacitor.
- 1-2. The capacitance values of high dielectric constant type capacitors change depending on the AC voltage applied. Please consider the AC voltage characteristics when selecting a capacitor to be used in a AC circuit.

#### 3.Applied Voltage

- 1. Do not apply a voltage to the capacitor that exceeds the rated voltage as called-out in the specifications.
- 1-1. Applied voltage between the terminals of a capacitor shall be less than or equal to the rated voltage.
- (1) When AC voltage is superimposed on DC voltage, the zero-to-peak voltage shall not exceed the rated DC voltage. When AC voltage or pulse voltage is applied, the peak-to-peak voltage shall not exceed the rated DC voltage.
- (2) Abnormal voltages (surge voltage, static electricity, pulse voltage, etc.) shall not exceed the rated DC voltage.

Typical voltage applied to the DC capacitor



(E : Maximum possible applied voltage.)

#### 1-2. Influence of overvoltage

Overvoltage that is applied to the capacitor may result in an electrical short circuit caused by the breakdown of the internal dielectric layers .

The time duration until breakdown depends on the applied voltage and the ambient temperature.

#### 4. Applied Voltage and Self-heating Temperature

- 1. When the capacitor is used in a high-frequency voltage, pulse voltage, application, be sure to take into account self-heating may be caused by resistant factors of the capacitor.
- 1-1. The load should be contained to the level such that when measuring at atomospheric temperature of 25°C, the product's self-heating remains below 20°C and surface temperature of the capacitor in the actual circuit remains wiyhin the maximum operating temperature.

### 5. DC Voltage and AC Voltage Characteristic

- 1. The capacitance value of a high dielectric constant type capacitor changes depending on the DC voltage applied. Please consider the DC voltage characteristics when a capacitor is selected for use in a DC circuit.
- 1-1. The capacitance of ceramic capacitors may change sharply depending on the applied voltage. (See figure) Please confirm the following in order to secure the capacitance.
- (1) Whether the capacitance change caused by the applied voltage is within the range allowed or not.

□ DC voltage characteristics

(2) In the DC voltage characteristics, the rate of capacitance change becomes larger as voltage increases. Even if the applied voltage is below the rated voltage. When a high dielectric constant type capacitor is in a circuit that needs a tight (narrow) capacitance tolerance. Example: a time constant circuit., please carefully consider the characteristics of these capacitors, such as their aging, voltage, and temperature characteristics. And check capacitors using your actual appliances at the intended environment and operating conditions.



2. The capacitance values of high dielectric constant type capacitors change depending on the AC voltage applied. Please consider the AC voltage characteristics when selecting a capacitor to be used in a AC circuit.





#### 6. Capacitance Aging

1. The high dielectric constant type capacitors have the characteristic in which the capacitance value decreases with the passage of time.

When you use a high dielectric constant type capacitors in a circuit that needs a tight (narrow) capacitance tolerance. Example: a time constant circuit., please carefully consider the characteristics of these capacitors, such as their aging, voltage, and temperature characteristics.

And check capacitors using your actual appliances at the intended environment and operating conditions.



#### 7. Vibration and Shock

- 1. The capacitors mechanical actress (vibration and shock) shall be specified for the use environment. Please confirm the kind of vibration and/or shock, its condition, and any generation of resonance. Please mount the capacitor so as not to generate resonance, and do not allow any impact on the terminals.
- 2. Mechanical shock due to falling may cause damage or a crack in the dielectric material of the capacitor. Do not use a fallen capacitor because the quality and reliability may be deteriorated.



3. When printed circuit boards are piled up or handled, the corners of another printed circuit board should not be allowed to hit the capacitor in order to avoid a crack or other damage to the capacitor.



#### ■ Soldering and Mounting

#### **1.Mounting Position**

- 1. Confirm the best mounting position and direction that minimizes the stress imposed on the capacitor during flexing or bending the printed circuit board.
- 1-1. Choose a mounting position that minimizes the stress imposed on the chip during flexing or bending of the board.

#### [Component Direction]



Locate chip horizontal to the direction in which stress acts

[Chip Mounting Close to Board Separation Point]



Chip arrangement Worst A-C-(B~D) Best

#### 2.Information before mounting

- 1. Do Not re-use capacitors that were removed from the equipment.
- 2. Confirm capacitance characteristics under actual applied voltage.
- 3. Confirm the mechanical stress under actual process and equipment use.
- 4. Confirm the rated capacitance, rated voltage and other electrical characteristics before assembly.
- 5. Prior to use, confirm the Solderability for the capacitors that were in long-term storage.
- 6. Prior to measuring capacitance, carry out a heat treatment for capacitors that were in long-term storage.
- 7.The use of Sn-Zn based solder will deteriorate the reliability of the MLCC.
  Please contact our sales representative or product engineers on the use of Sn-Zn based solder in advance.

#### 3. Maintenance of the Mounting (pick and place) Machine

- 1. Make sure that the following excessive forces are not applied to the capacitors.
- 1-1. In mounting the capacitors on the printed circuit board, any bending force against them shall be kept to a minimum to prevent them from any bending damage or cracking. Please take into account the following precautions and recommendations for use in your process.
- (1) Adjust the lowest position of the pickup nozzle so as not to bend the printed circuit board.
- (2) Adjust the nozzle pressure within a static load of 1N to 3N during mounting.



2.Dirt particles and dust accumulated between the suction nozzle and the cylinder inner wall prevent the nozzle from moving smoothly. This imposes greater force upon the chip during mounting, causing cracked chips. Also the locating claw, when worn out, imposes uneven forces on the chip when positioning, causing cracked chips. The suction nozzle and the locating claw must be maintained, checked and replaced periodically.





#### 4-1.Reflow Soldering

- 1. When sudden heat is applied to the components, the mechanical strength of the components will decrease because a sudden temperature change causes deformation inside the components. In order to prevent mechanical damage to the components, preheating is required for both the components and the PCB board. Preheating conditions are shown in table 1. It is required to keep the temperature differential between the solder and the components surface ( $\Delta T$ ) as small as possible.
- Solderability of Tin plating termination chips might be deteriorated when a low temperature soldering profile where the peak solder temperature is below the melting point of Tin is used. Please confirm the Solderability of Tin plated termination chips before use.
- When components are immersed in solvent after mounting be sure to maintain the temperature difference (ΔT) between the component and the solvent within the range shown in the table 1.

Table 1

Part Number	Temperature Differential
GC□03/15/18/21/31	ΔΤ≦190°C
GC□32	ΔΤ≦130°C

#### **Recommended Conditions**

	Pb-Sn	Lead Free Solder	
	Infrared Reflow	Vapor Reflow	Lead Free Solder
Peak Temperature	230~250°C	230~240°C	240~260°C
Atmosphere	Air	Air	Air or N2

Pb-Sn Solder: Sn-37Pb

Lead Free Solder: Sn-3.0Ag-0.5Cu

- 4. Optimum Solder Amount for Reflow Soldering
- 4-1. Overly thick application of solder paste results in a excessive solder fillet height. This makes the chip more susceptible to mechanical and thermal stress on the board and may cause the chips to crack.
- 4-2. Too little solder paste results in a lack of adhesive strength on the outer electrode, which may result in chips breaking loose from the PCB.

#### [Standard Conditions for Reflow Soldering]

#### Infrared Reflow



Vapor Reflow



#### [Allowable Soldering Temperature and Time]



In case of repeated soldering, the accumulated soldering time must be within the range shown above.



\* GC □ 03: 1/3 of Chip Thickness min.

in section

4-3. Make sure the solder has been applied smoothly to the end surface to a height of 0.2mm\* min.

Inverting the PCB

Make sure not to impose any abnormal mechanical shocks to the PCB.

#### 4-2.Flow Soldering

- 1. When sudden heat is applied to the components, the mechanical strength of the components will decrease because a sudden temperature change causes deformation inside the components. In order to prevent mechanical damage in the components, preheating should be required for both of the components and the PCB board. Preheating conditions are shown in table 2. It is required to keep temperature differential between the solder and the components surface (ΔT) as small as possible.
- Excessively long soldering time or high soldering temperature can result in leaching of the outer electrodes, causing poor adhesion or a reduction in capacitance value due to loss of contact between electrodes and end termination.
- 3. When components are immersed in solvent after mounting, be sure to maintain the temperature difference ( $\Delta T$ ) between the component and solvent within the range shown in the table 2.
- 4. Do not apply flow soldering to chips not listed in Table 2.

Table 2

140.02		
Part Number	Temperature Differential	
GC□18/21/31	ΔΤ≦150°C	

#### **Recommended Conditions**

	Pb-Sn Solder	Lead Free Solder
Preheating Peak Temperature	90~110°C	100∼120°C
Soldering Peak Temperature	240~250°C	250~260°C
Atmosphere	Air	N <sub>2</sub>

Pb-Sn Solder: Sn-37Pb Lead Free Solder: Sn-3.0Ag-0.5Cu

- 5. Optimum Solder Amount for Flow Soldering
- 5-1. The top of the solder fillet should be lower than the thickness of components. If the solder amount is excessive, the risk of cracking is higher during board bending or any other stressful condition.

#### [Standard Conditions for Flow Soldering]



#### [Allowable Soldering Temperature and Time]



In case of repeated soldering, the accumulated soldering time must be within the range shown above.



#### 4-3. Correction with a Soldering Iron

- 1. When sudden heat is applied to the components when using a soldering iron, the mechanical strength of the components will decrease because the extreme temperature change can cause deformations inside the components. In order to prevent mechanical damage to the components, preheating is required for both the components and the PCB board. Preheating conditions, (The "Temperature of the Soldering Iron tip", "Preheating Temperature", "Temperature Differential" between the iron tip and the components and the PCB), should be within the conditions of table 3. It is required to keep the temperature differential between the soldering Iron and the component surfaces (ΔT) as small as possible.
- 2. After soldering, do not allow the component/PCB to rapidly cool down.
- 3. The operating time for the re-working should be as short as possible. When re-working time is too long, it may cause solder leaching, and that will cause a reduction in the adhesive strength of the terminations.

Table 3

Part Number	Temperature of Soldering Iron tip	Preheating Temperature	Temperature Differential (ΔT)	Atmosphere
GC□03/15/18/21/31	350°C max.	150°C min.	ΔT≦190°C	Air
GC□32	280°C max.	150°C min.	ΔT≦130°C	Air

<sup>\*</sup>Applicable for both Pb-Sn and Lead Free Solder Pb-Sn Solder: Sn-37Pb

Lead Free Solder: Sn-3.0Ag-0.5Cu

- 4. Optimum Solder amount when re-working with a Soldering Iron
- 4-1. In case of sizes smaller than 0603, (GC□03/15/18), the top of the solder fillet should be lower than 2/3's of the thickness of the component or 0.5mm whichever is smaller. In case of 0805 and larger sizes, (GC□21/31/32), the top of the solder fillet should be lower than 2/3's of the thickness of the component. If the solder amount is excessive, the risk of cracking is higher during board bending or under any other stressful condition.



in section

- 4-2. A Soldering iron with a tip of ø3mm or smaller should be used. It is also necessary to keep the soldering iron from touching the components during the re-work.
- 4-3. Solder wire with Ø0.5mm or smaller is required for soldering.

#### **4-4.Leaded Component Insertion**

 If the PCB is flexed when leaded components (such as transformers and ICs) are being mounted, chips may crack and solder joints may break.
 Before mounting leaded components, support the PCB using backup pins or special jigs to prevent warping.



#### 5.Washing

Excessive ultrasonic oscillation during cleaning can cause the PCBs to resonate, resulting in cracked chips or broken solder joints. Take note not to vibrate PCBs.

#### **6.Electrical Test on Printed Circuit Board**

- 1. Confirm position of the support pin or specific jig, when inspecting the electrical performance of a capacitor after mounting on the printed circuit board.
- 1-1. Avoid bending printed circuit board by the pressure of a test pin, etc.

  The thrusting force of the test probe can flex the PCB, resulting in cracked chips or open solder joints.

  Provide support pins on the back side of the PCB to prevent warping or flexing.
- 1-2. Avoid vibration of the board by shock when a test pin contacts a printed circuit board.



#### 7.Printed Circuit Board Cropping

- 1. After mounting a capacitor on a printed circuit board, do not apply any stress to the capacitor that is caused by bending or twisting the board.
- 1-1. In cropping the board, the stress as shown right may cause the capacitor to crack. Try not to apply this type of stress to a capacitor.



- 2. Check of the cropping method for the printed circuit board in advance.
- 2-1. Printed circuit board cropping shall be carried out by using a jig or an apparatus to prevent the mechanical stress which can occur to the board.
  - (1) Example of a suitable jig

Recommended example: the board should be pushed as close to the near the cropping jig as possible and from the back side of board in order to minimize the compressive stress applied to capacitor. Not recommended example\* when the board is pushed at a point far from the cropping jig and from the front side of board as below, the capacitor may form a crack caused by the tensile stress applied to capacitor.



(2) Example of a suitable machine

An outline of a printed circuit board cropping machine is shown as follows. Along the lines with the V-grooves on printed circuit board, the top and bottom blades are aligned to one another when cropping the board.

The misalignment of the position between top and bottom blades may cause the capacitor to crack.





#### Others

#### 1. Under Operation of Equipment

- 1-1. Do not touch a capacitor directly with bare hands during operation in order to avoid the danger of a electric shock.
- 1-2. Do not allow the terminals of a capacitor to come in contact with any conductive objects (short-circuit). Do not expose a capacitor to a conductive liquid, inducing any acid or alkali solutions.
- 1-3. Confirm the environment in which the equipment will operation is under the specified conditions. Do not use the equipment under the following environment.
  - (1) Being spattered with water or oil.
  - (2) Being exposed to direct sunlight.
  - (3) Being exposed to Ozone, ultraviolet rays or radiation.
  - (4) Being exposed to toxic gas (e.g., hydrogen sulfide, sulfur dioxide, chlorine, ammonia gas etc.)
  - (5) Any vibrations or mechanical shocks exceeding the specified limits.
  - (6) Moisture condensing environments.
- 1-4. Use damp proof countermeasures if using under any conditions that can cause condensation.

#### 2. Others

#### 2-1. In an Emergency

- (1) If the equipment should generate smoke, fire or smell, immediately turn off or unplug the equipment. If the equipment is not turned off or unplugged, the hazards may be worsened by supplying continuous power.
- (2) In this type of situation, do not allow face and hands to come in contact with the capacitor or burns may be caused by the capacitors high temperature.

#### 2-2. Disposal of waste

When capacitors are disposed, they must be burned or buried by the industrial waste vender with the appropriate licenses.

#### 2-3. Circuit Design

GC□ Series capacitors in this specification are not safety recognized products.

#### 2-4. Remarks

Failure to follow the cautions may result, worst case, in a short circuit and smoking when the product is used. The above notices are for standard applications and conditions. Contact us when the products are used in special mounting conditions.

Select optimum conditions for operation as they determine the reliability of the product after assembly. The data herein are given in typical values, not guaranteed ratings.

#### Rating

#### **1.Operating Temperature**

- 1. The operating temperature limit depends on the capacitor.
- 1-1.Do not apply temperatures exceeding the upper operating temperature.
  - It is necessary to select a capacitor with a suitable rated temperature which will cover the operating temperature range.
  - Also it is necessary to consider the temperature distribution in equipment and the seasonal temperature variable factor.
- 1-2. Consider the self-heating of the capacitor
  - The surface temperature of the capacitor shall be the upper operating temperature or less when including the self-heating factors.

#### 2. Atmosphere surroundings (gaseous and liquid)

- 1. Restriction on the operating environment of capacitors.
- 1-1. The capacitor, when used in the above, unsuitable, operating environments may deteriorate due to the corrosion of the terminations and the penetration of moisture into the capacitor.
- 1-2. The same phenomenon as the above may occur when the electrodes or terminals of the capacitor are subject to moisture condensation.
- 1-3. The deterioration of characteristics and insulation resistance due to the oxidization or corrosion of terminal electrodes may result in breakdown when the capacitor is exposed to corrosive or volatile gases or solvents for long periods of time.

#### 3.Piezo-electric Phenomenon

1. When using high dielectric constant type capacitors in AC or pulse circuits, the capacitor itself vibrates at specific frequencies and noise may be generated.

Moreover, when the mechanical vibration or shock is added to capacitor, noise may occur.

#### ■ Soldering and Mounting

#### 1.PCB Design

- 1. Notice for Pattern Forms
- 1-1. Unlike leaded components, chip components are susceptible to flexing stresses since they are mounted directly on the substrate.

They are also more sensitive to mechanical and thermal stresses than leaded components. Excess solder fillet height can multiply these stresses and cause chip cracking. When designing substrates, take land patterns and dimensions into consideration to eliminate the possibility of excess solder fillet height.

1-2. It is possible for the chip to crack by the expansion and shrinkage of a metal board.

Please contact us if you want to use our ceramic capacitors on a metal board such as Aluminum.

#### Pattern Forms

Pattern Forms	Prohibited	Correct
Placing Close to Chassis	Chassis Solder (ground) Electrode Pattern	Solder Resist
Placing of Chip Components and Leaded Components	Lead Wire	Solder Resist
Placing of Leaded Components after Chip Component	Soldering Iron Lead Wire	Solder Resist
Lateral Mounting		Solder Resist

#### 2. Land Dimensions

2-1. Chip capacitor can be cracked due to the stress of PCB bending / etc if the land area is larger than needed and has an excess amount of solder.

Please refer to the land dimensions in table 1 for flow soldering, table 2 for reflow soldering.



Please confirm the suitable land dimension by evaluating of the actual SET / PCB.

Table 1 Flow Soldering Method

Table 11 low Soldering Method				
Dimensions Part Number	Chip (L×W)	а	b	С
GC□18	1.6×0.8	0.6~1.0	0.8~0.9	0.6~0.8
GC□21	2.0×1.25	1.0~1.2	0.9~1.0	0.8~1.1
GC□31	3.2×1.6	2.2~2.6	1.0~1.1	1.0~1.4
				(' )

(in mm)

Table 2 Reflow Soldering Method

Dimensions Part Number	Chip (L×W)	а	b	С
GC□03	0.6×0.3	0.2~0.3	0.2~0.35	0.2~0.4
GC□15	1.0×0.5	0.3~0.5	0.35~0.45	0.4~0.6
GC□18	1.6×0.8	0.6~0.8	0.6~0.7	0.6~0.8
GC□21	2.0×1.25	1.0~1.2	0.6~0.7	0.8~1.1
GC□31	3.2×1.6	2.2~2.4	0.8~0.9	1.0~1.4
GC□32	3.2×2.5	2.0~2.4	1.0~1.2	1.8~2.3

(in mm)



#### 2.Adhesive Application

Thin or insufficient adhesive can cause the chips to loosen or become disconnected during flow soldering.
The amount of adhesive must be more than dimension c, shown in the drawing at right, to obtain
the correct bonding strength.

The chip's electrode thickness and land thickness must also be taken into consideration.



- 2. Low viscosity adhesive can cause chips to slip after mounting. The adhesive must have a viscosity of 5000Pa s (500ps) min. (at 25°C)
- 3. Adhesive Coverage

Part Number	Adhesive Coverage*
GC□18	0.05mg min.
GC□21	0.1mg min.
GC□31	0.15mg min.

\*Nominal Value

#### 3.Adhesive Curing

Insufficient curing of the adhesive can cause chips to disconnect during flow soldering and causes
deterioration in the insulation resistance between the outer electrodes due to moisture absorption.
Control curing temperature and time in order to prevent insufficient hardening.

#### 4.Flux Application

- 1. An excessive amount of flux generates a large quantity of flux gas, which can cause a deterioration of Solderability.
  - So apply flux thinly and evenly throughout. (A foaming system is generally used for flow soldering).
- 2. Flux containing too a high percentage of halide may cause corrosion of the outer electrodes unless there is sufficient cleaning. Use flux with a halide content of 0.2% max.
- 3. Do not use strong acidic flux.
- Do not use water-soluble flux.
   (\*Water-soluble flux can be defined as non rosin type flux including wash-type flux and non-wash-type flux.)

#### 5.Flow Soldering

Set temperature and time to ensure that leaching of the outer electrode does not exceed 25% of the chip end area as a single chip (full length of the edge A-B-C-D shown right) and 25% of the length A-B shown below as mounted on substrate.



#### 6.Washing

- 1. Please evaluate a capacitor by actual cleaning equipment and condition surely for confirming the quality and select the applicable solvent.
- 2. Unsuitable cleaning solvent may leave residual flux, other foreign substances, causing deterioration of electrical characteristics and the reliability of the capacitors.
- 3. Select the proper cleaning conditions.
- 3-1. Improper cleaning conditions (excessive or insufficient) may result in the deterioration of the performance of the capacitors.

#### 7.Coating

1. A crack may be caused in the capacitor due to the stress of the thermal contraction of the resin during curing process.

The stress is affected by the amount of resin and curing contraction.

Select a resin with small curing contraction.

The difference in the thermal expansion coefficient between a coating resin or a molding resin and capacitor may cause the destruction and deterioration of the capacitor such as a crack or peeling, and lead to the deterioration of insulation resistance or dielectric breakdown.

Select a resin for which the thermal expansion coefficient is as close to that of capacitor as possible.

A silicone resin can be used as an under-coating to buffer against the stress.

2. Select a resin that is less hygroscopic.

Using hygroscopic resins under high humidity conditions may cause the deterioration of the insulation resistance of a capacitor.

An epoxy resin can be used as a less hygroscopic resin.

#### ■ Others

#### 1.Transportation

- 1. The performance of a capacitor may be affected by the conditions during transportation.
- 1-1. The capacitors shall be protected against excessive temperature, humidity and mechanical force during transportation.
- (1) Climatic condition
  - low air temperature : −40°C
  - change of temperature air/air : -25°C/+25°C
  - low air pressure : 30 kPa
  - change of air pressure : 6 kPa/min
- (2) Mechanical condition

Transportation shall be done in such a way that the boxes are not deformed and forces are not directly passed on to the inner packaging.

- 1-2. Do not apply excessive vibration, shock, and pressure to the capacitor.
- (1) When excessive mechanical shock or pressure is applied to a capacitor, chipping or cracking may occur in the ceramic body of the capacitor.
- (2) When a sharp edge of an air driver, a soldering iron, tweezers, a chassis, etc. impacts strongly on the surface of capacitor, the capacitor may crack and short-circuit.
- 1-3. Do not use a capacitor to which excessive shock was applied by dropping etc. The capacitor dropped accidentally during processing may be damaged.



### **∧** NOTE

- 1.Please make sure that your product has been evaluated in view of your specifications with our product being mounted to your product.
- 2. Your are requested not to use our product deviating from this product specification.
- 3.We consider it not appropriate to include any terms and conditions with regard to the business transaction in the product specifications, drawings or other technical documents. Therefore, if your technical documents as above include such terms and conditions such as warranty clause, product liability clause, or intellectual property infringement liability clause, they will be deemed to be invalid.